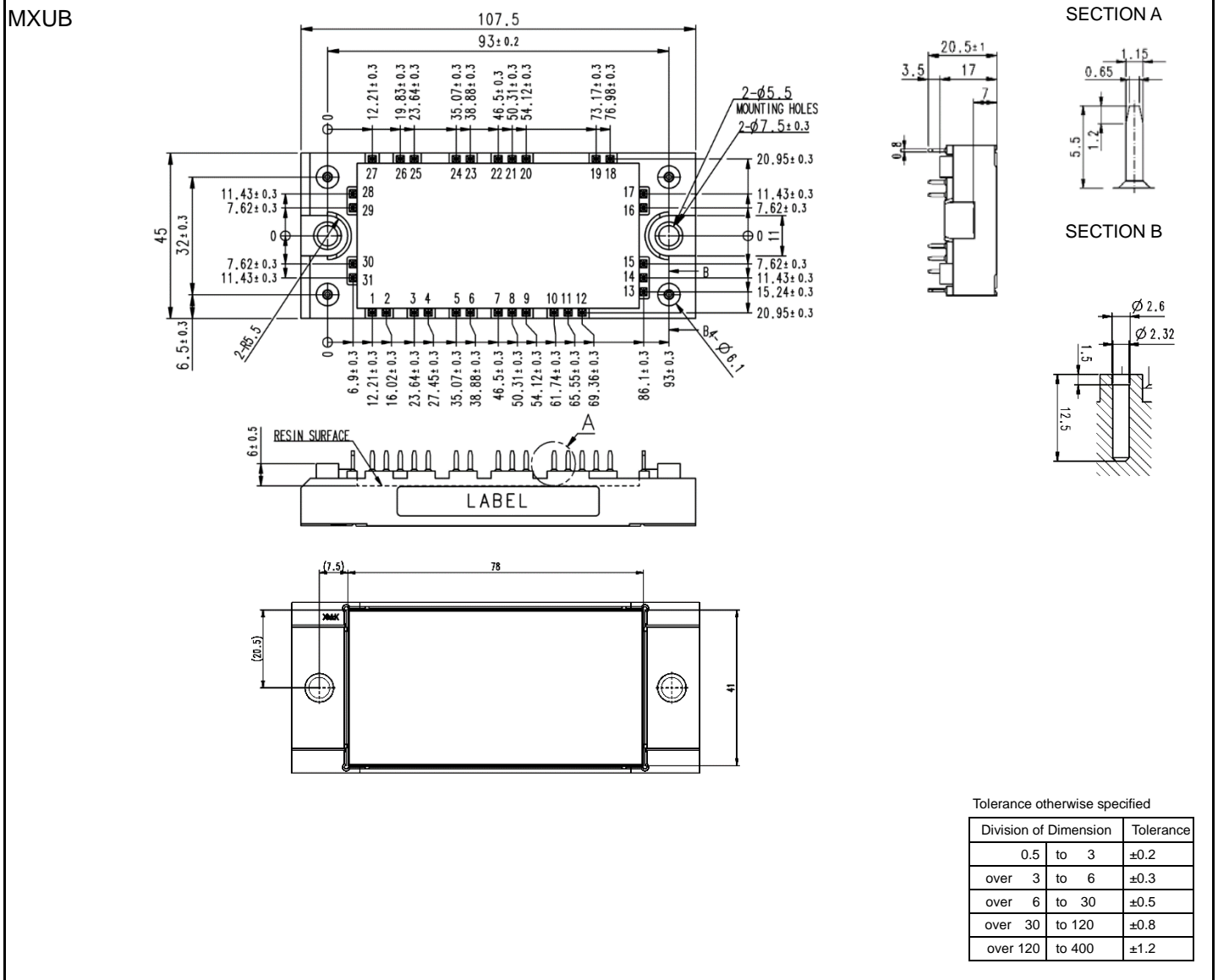


CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING

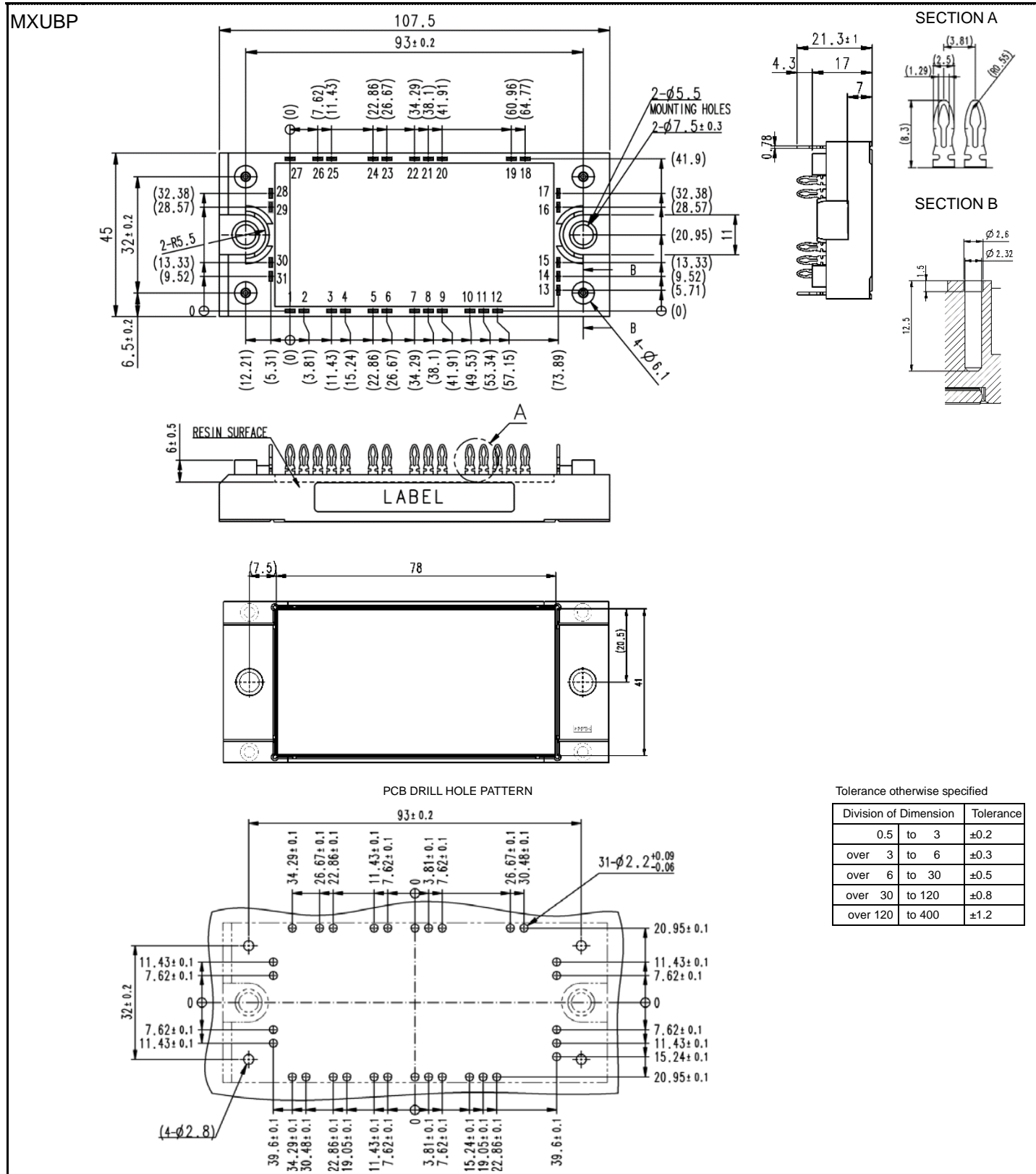
Dimension in mm



CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING



CM75MXUB-24T/CM75MXUBP-24THIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)****INVERTER PART IGBT/FWD**

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =120 °C (Note2, 4)	75	A
I _{CRM}		Pulse, Repetitive (Note3)	150	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	440	W
I _E (Note1)	Emitter current	DC (Note2)	75	A
I _{ERM} (Note1)		Pulse, Repetitive (Note3)	150	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =125 °C (Note2, 4)	50	A
I _{CRM}		Pulse, Repetitive (Note3)	100	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	330	W
V _{RRM}	Repetitive peak reverse voltage	G-E short-circuited	1200	V
I _F	Forward current	DC (Note2)	35	A
I _{FRM}		Pulse, Repetitive (Note3)	70	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

CONVERTER PART DIODE

Symbol	Item	Conditions	Rating	Unit	
V _{RRM}	Repetitive peak reverse voltage	-	1600	V	
E _a	Recommended AC input voltage	RMS	440	V	
I _o	DC output current	3-phase full wave rectifying, T _C =125 °C (Note4)	75	A	
I _{FSM}	Surge forward current	The sine half wave 1 cycle peak value, f=60 Hz, non-repetitive	T _{vj} =25 °C	900	A
			T _{vj} =150 °C	720	
I ² _t	Current square time	Value for one cycle of surge current	T _{vj} =25 °C	3375	A ² s
			T _{vj} =150 °C	2160	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	150	°C	

MODULE

Symbol	Item	Conditions	Rating	Unit
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T _{Cmax}	Maximum case temperature	(Note4)	125	°C
T _{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +125	

CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE**ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)**
INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =7.5 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.70	2.15	V
			T _{vj} =125 °C	-	2.00	-	
			T _{vj} =150 °C	-	2.05	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.60	1.85	V
			T _{vj} =125 °C	-	1.75	-	
			T _{vj} =150 °C	-	1.80	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	18.2	nF	
C _{oes}	Output capacitance		-	-	0.5		
C _{res}	Reverse transfer capacitance		-	-	0.2		
Q _G	Gate charge	V _{CC} =600 V, I _C =75 A, V _{GE} =15 V	-	0.57	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =600 V, I _C =75 A, V _{GE} =±15 V, R _G =5.6 Ω, Inductive load	-	-	500	ns	
t _r	Rise time		-	-	150		
t _{d(off)}	Turn-off delay time		-	-	500		
t _f	Fall time		-	-	400		
V _{EC} (Note1) (Terminal)	Emitter-collector voltage	I _E =75 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.75	2.35	V
			T _{vj} =125 °C	-	1.95	-	
			T _{vj} =150 °C	-	2.00	-	
V _{EC} (Note1) (Chip)	Emitter-collector voltage	I _E =75 A, G-E short-circuited, (Note5)	T _{vj} =25 °C	-	1.65	2.10	V
			T _{vj} =125 °C	-	1.65	-	
			T _{vj} =150 °C	-	1.65	-	
t _{rr} (Note1)	Reverse recovery time	V _{CC} =600 V, I _E =75 A, V _{GE} =±15 V,	-	-	400	ns	
Q _{rr} (Note1)	Reverse recovery charge	R _G =5.6 Ω, Inductive load	-	7.5	-	μC	
E _{on}	Turn-on switching energy per pulse	V _{CC} =600 V, I _C =I _E =75 A,	-	8.7	-	mJ	
E _{off}	Turn-off switching energy per pulse	V _{GE} =±15 V, R _G =5.6 Ω, T _{vj} =150 °C,	-	9.0	-		
E _{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	4.3	-	mJ	
r _g	Internal gate resistance	Per switch	-	4	-	Ω	

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =5.0 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =50 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.70	2.15	V
			T _{vj} =125 °C	-	1.95	-	
			T _{vj} =150 °C	-	2.00	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =50 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.60	1.85	V
			T _{vj} =125 °C	-	1.75	-	
			T _{vj} =150 °C	-	1.80	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	12.1	nF	
C _{oes}	Output capacitance		-	-	0.4		
C _{res}	Reverse transfer capacitance		-	-	0.2		
Q _G	Gate charge	V _{CC} =600 V, I _C =50 A, V _{GE} =15 V	-	0.38	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =600 V, I _C =50 A, V _{GE} =±15 V, R _G =15 Ω, Inductive load	-	-	300	ns	
t _r	Rise time		-	-	150		
t _{d(off)}	Turn-off delay time		-	-	500		
t _f	Fall time		-	-	400		

CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPEELECTRICAL CHARACTERISTICS (cont.; $T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $T_{vj}=150\text{ }^{\circ}\text{C}$, Inductive load	$I_C=50\text{ A}$, $R_G=15\text{ }\Omega$	-	3.9	-	mJ	
E_{off}	Turn-off switching energy per pulse			-	5.4	-		
E_{rr}	Reverse recovery energy per pulse			$I_E=50\text{ A}$, $R_G=15\text{ }\Omega$	-	2.4		-
r_g	Internal gate resistance	-	-	0	-	Ω		
I_{RRM}	Reverse current	$V_R=V_{RRM}$, G-E short-circuited	-	-	1.0	mA		
V_F (Terminal)	Forward voltage	$I_F=35\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.70	2.30	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.90	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.95	-	
V_F (Chip)	Forward voltage	$I_F=35\text{ A}$, G-E short-circuited, (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.65	2.10	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.65	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.65	-	
t_{rr}	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_F=35\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	400	ns		
Q_{rr}	Reverse recovery charge	$R_G=20\text{ }\Omega$, Inductive load	-	3.5	-	μC		

CONVERTER PART DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $T_{vj}=150\text{ }^{\circ}\text{C}$	-	-	20	mA		
V_F (Terminal)	Forward voltage	$I_F=75\text{ A}$		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.25	1.70	V
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.20	-	
V_F (chip)				$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.15	1.40	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.10	-	

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100}=493\text{ }\Omega$, $T_C=100\text{ }^{\circ}\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	339	K/kW	
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)	-	-	628		
$R_{th(j-c)Q}$		Junction to case, Brake IGBT (Note4)	-	-	452		
$R_{th(j-c)D}$		Junction to case, Brake DIODE (Note4)	-	-	1070		
$R_{th(j-c)D}$		Junction to case, per Converter DIODE (Note4)	-	-	650		
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module,	Thermal grease applied (Note4, 7)	-	20.2	-	K/kW
			PC-TIM applied (Note4, 8)	-	5.5	-	

CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
M_s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m	
d_s	Creepage distance	Solder pin type(MXUB)	Terminal to terminal	10.9	-	-	mm
			Terminal to base plate	18.3	-	-	
		Pressfit pin type(MXUBP)	Terminal to terminal	5.2	-	-	
			Terminal to base plate	16.1	-	-	
d_a	Clearance	Solder pin type(MXUB)	Terminal to terminal	6.5	-	-	mm
			Terminal to base plate	13.1	-	-	
		Pressfit pin type(MXUBP)	Terminal to terminal	5.0	-	-	
			Terminal to base plate	16.1	-	-	
e_c	Flatness of base plate	On the centerline X, Y (Note9)	±0	-	+200	µm	
m	mass	-	-	165	-	g	

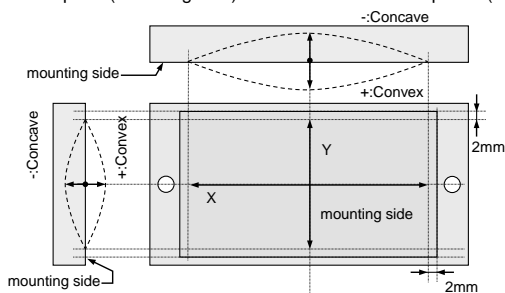
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across P-N(P1-N1) terminals	-	600	850	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G*P*/G*N-E/GB-E terminals (*=U,V,W)	13.5	15.0	16.5	V
R_G	External gate resistance	Inverter IGBT, Per switch	5.6	-	56	Ω
		Brake IGBT	15	-	150	

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$
 R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25}=25\text{ [°C]}+273.15=298.15$ [K]
 R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50}=50\text{ [°C]}+273.15=323.15$ [K]
- Typical value is measured by using thermally conductive grease of $\lambda=0.9\text{ W/(m·K)}/D_{(C-S)}=50\text{ }\mu\text{m}$.
- Typical value is measured by using PC-TIM of $\lambda=3.4\text{ W/(m·K)}/D_{(C-S)}=50\text{ }\mu\text{m}$.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



- Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.6

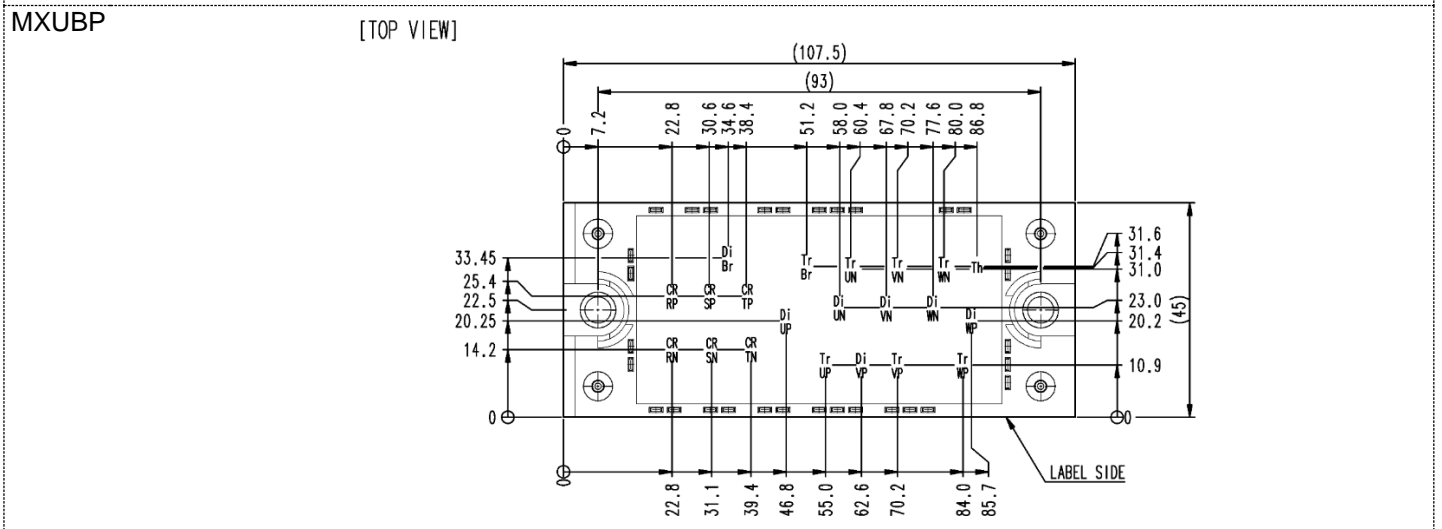
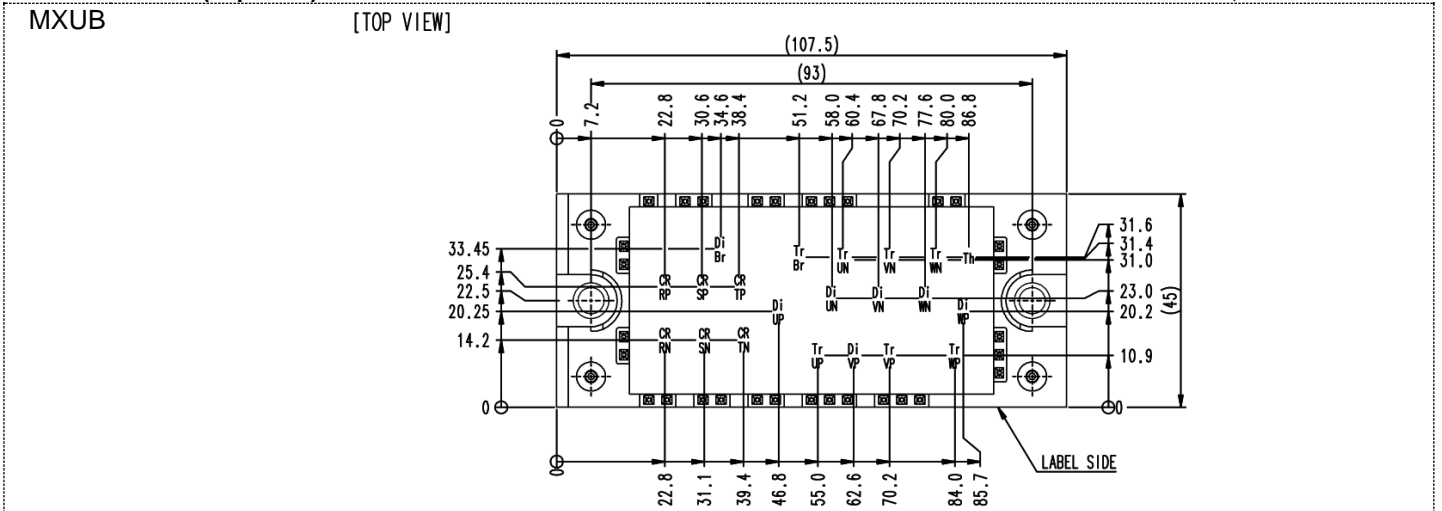
Type	Manufacturer	Size	Tightening torque (N·m)	Recommended tightening method
(1) PT®	EJOT	K25x8	0.55 ± 0.055	by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver)
(2) PT®		K25x10	0.75 ± 0.075 N·m	
(3) DELTA PT®		25x8	0.55 ± 0.055 N·m	
(4) DELTA PT®		25x10	0.75 ± 0.075 N·m	
(5) B1 tapping screw	-	φ2.6x10	0.75 ± 0.075 N·m	
		φ2.6x12		

CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

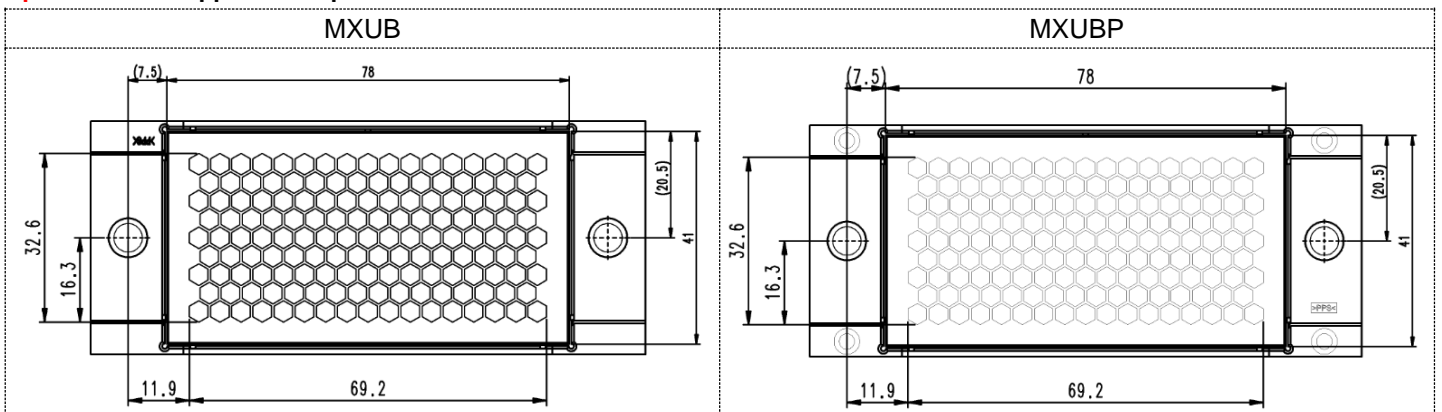
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm



Tr*P/Tr*N/Tr*Br: IGBT, Di*P/Di*N: DIODE (*=U/V/W), Di*Br: BRAKE DIODE,
CR*P/CR*N: CONVERTER DIODE (*=R/S/T), Th: NTC thermistor

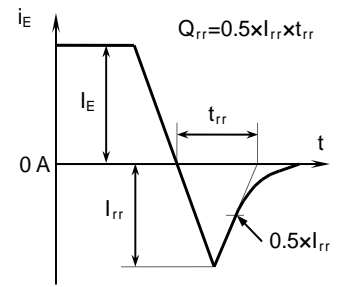
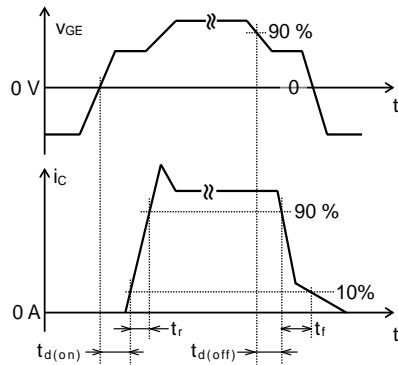
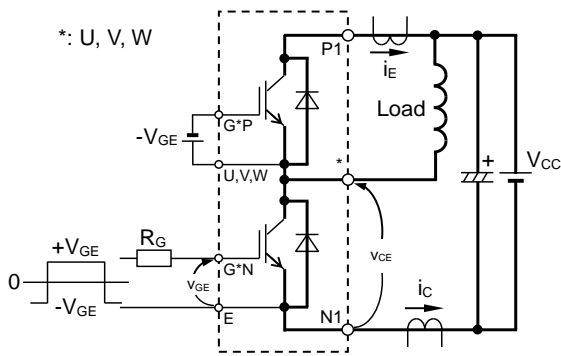
Option: PC-TIM applied baseplate outline



CM75MXUB-24T/CM75MXUBP-24T

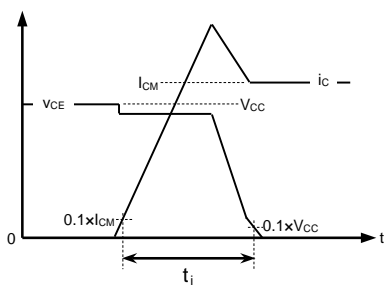
HIGH POWER SWITCHING USE
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS

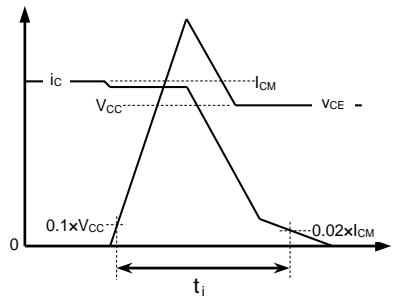


Switching characteristics test circuit and waveforms

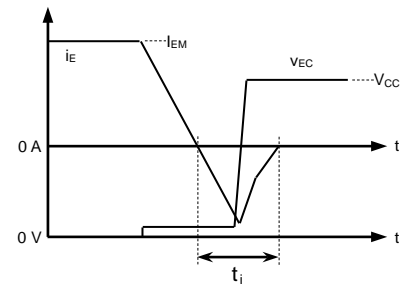
t_{rr} , Q_{rr} characteristics test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



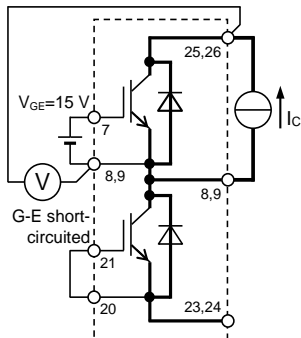
FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

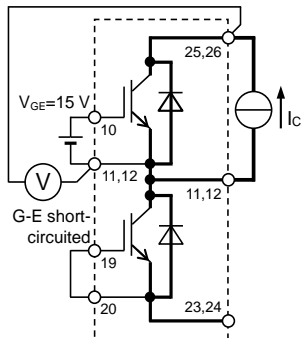
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

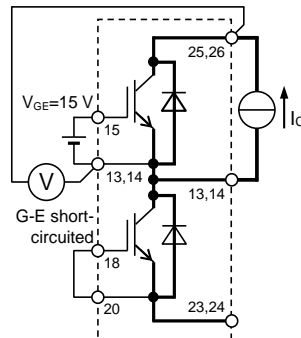
TEST CIRCUIT



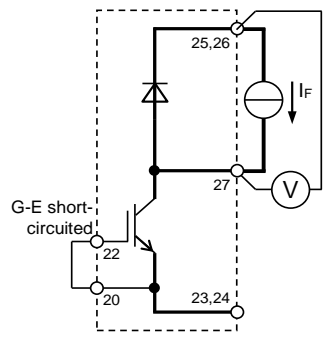
TrUP



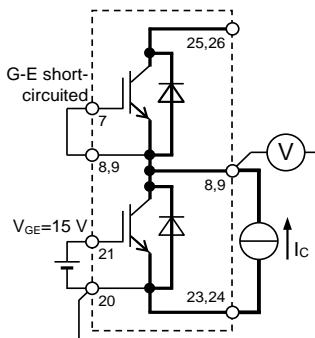
TrVP



TrWP

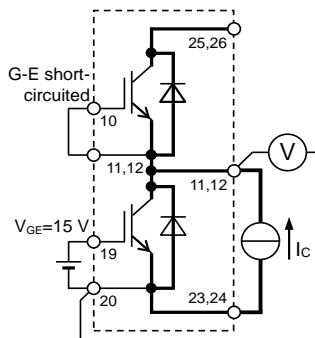


Brake DIODE



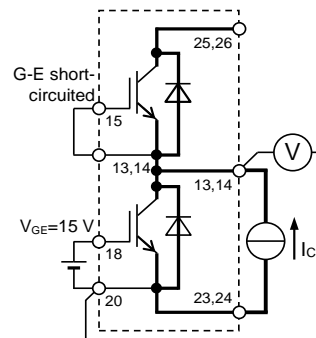
TrUN

Gate-emitter GVP-V, GVN-E,
short-circuited GWP-W, GWN-E
GB-E



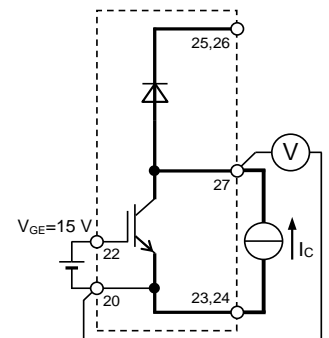
TrVN

Gate-emitter GUP-U, GUN-E,
short-circuited GWP-W, GWN-E
GB-E



TrWN

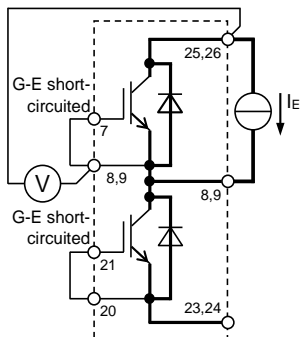
Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E
GB-E



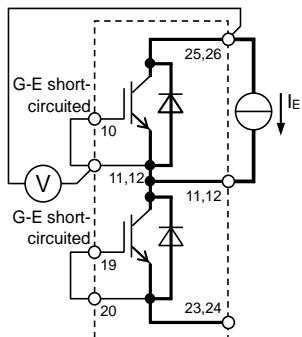
Brake IGBT

Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E,
GWP-W, GWN-E

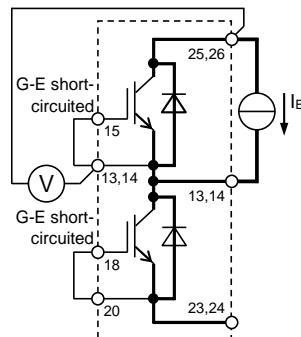
V_{CEsat} /BRAKE DIODE V_F characteristics test circuit



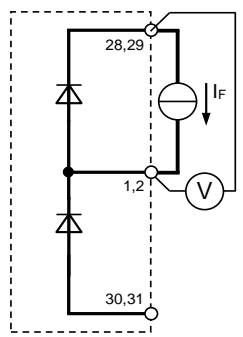
DiUP



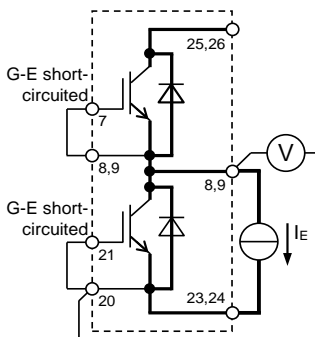
DiVP



DiWP

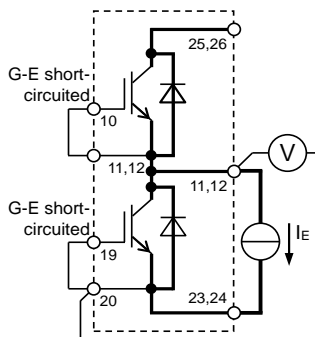


CONVERTER DIODE (ex.phase-R)



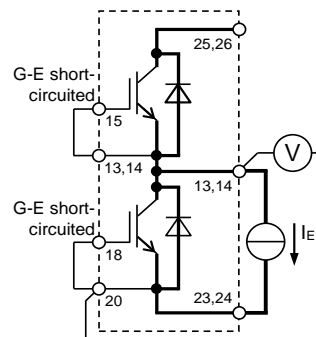
DiUN

Gate-emitter GVP-V, GVN-E,
short-circuited GWP-W, GWN-E
GB-E



DiVN

Gate-emitter GUP-U, GUN-E,
short-circuited GWP-W, GWN-E
GB-E



DiWN

Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E
GB-E

V_{EC} / CONVERTER DIODE V_F characteristics test circuit

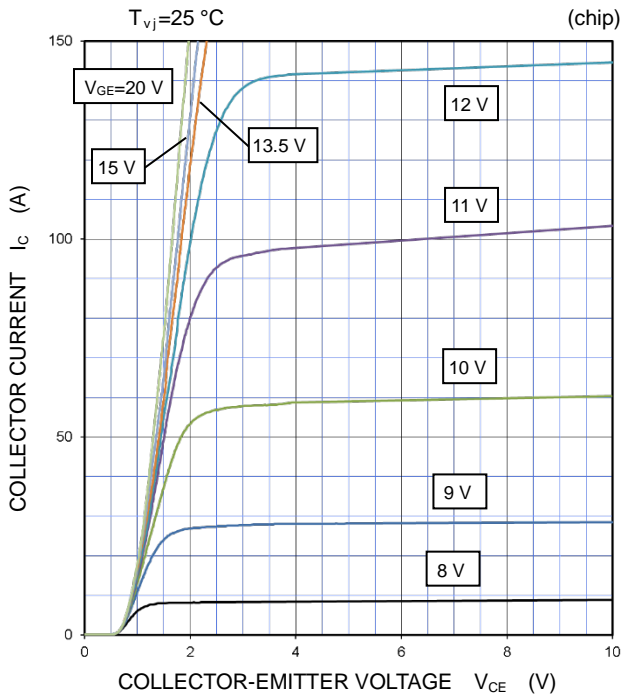
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

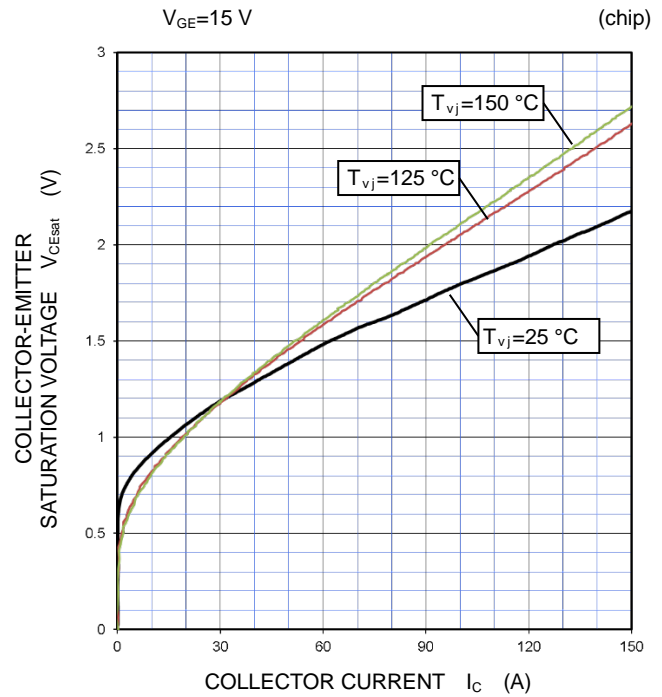
PERFORMANCE CURVES

INVERTER PART

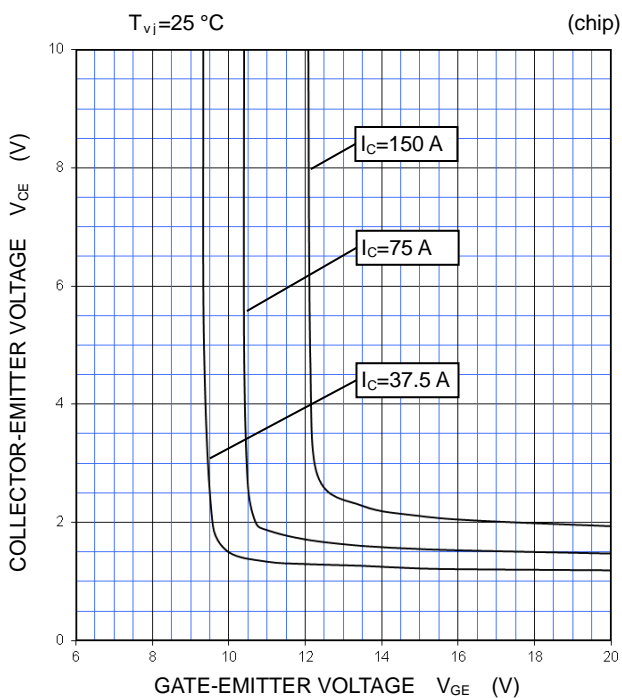
OUTPUT CHARACTERISTICS (TYPICAL)



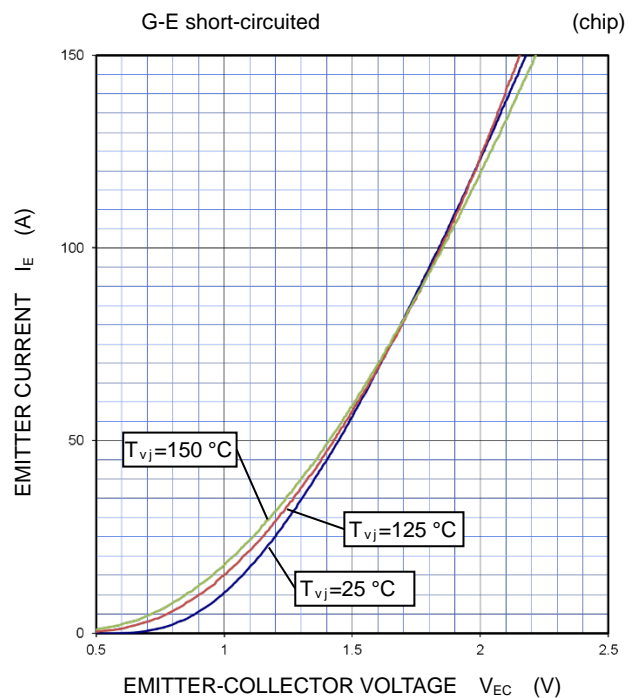
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



CM75MXUB-24T/CM75MXUBP-24T

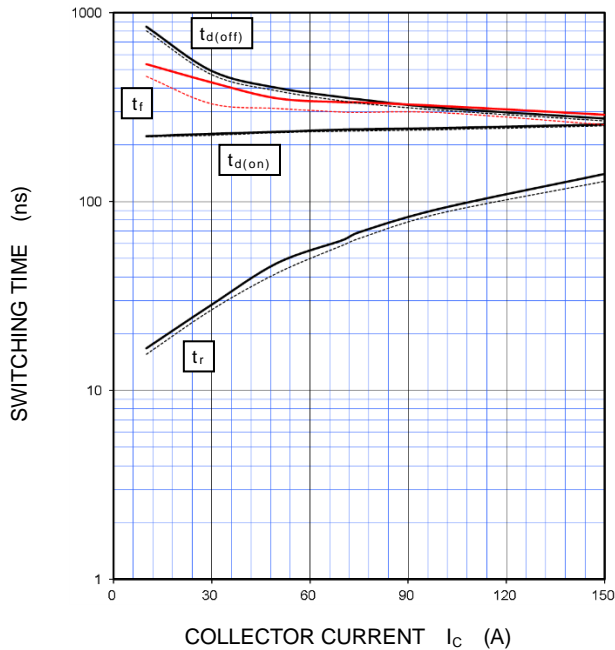
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

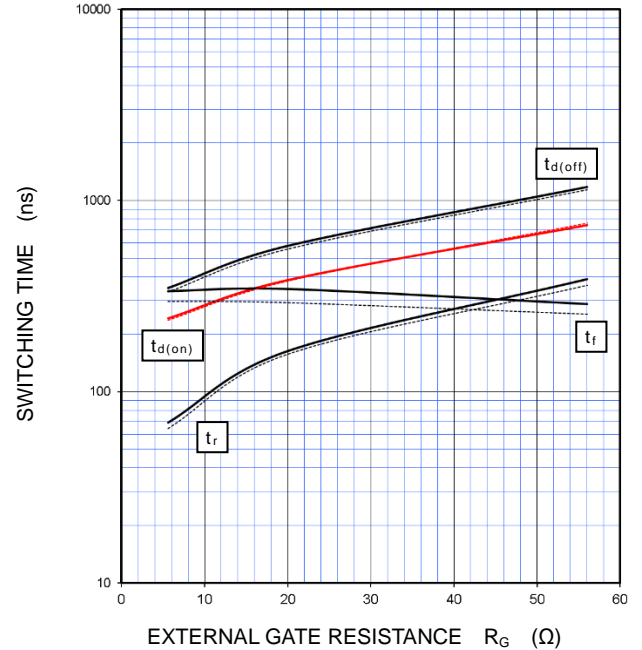
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $R_G=5.6\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



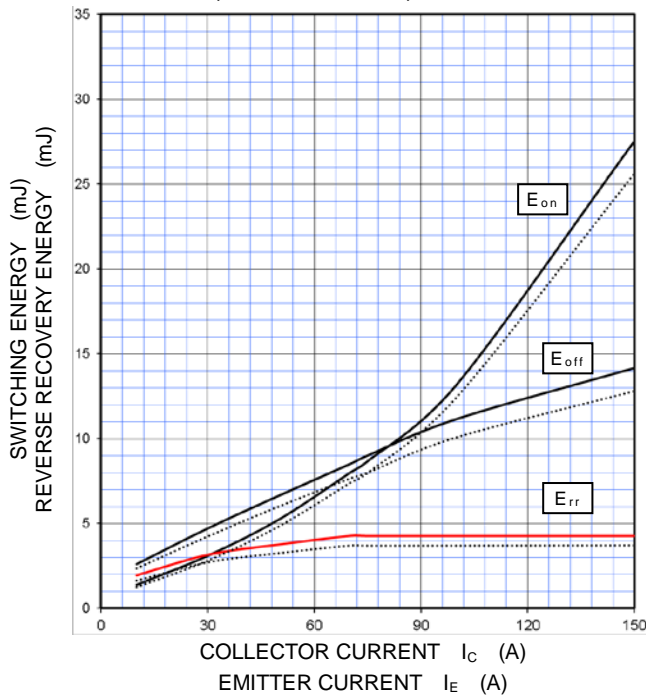
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_c=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



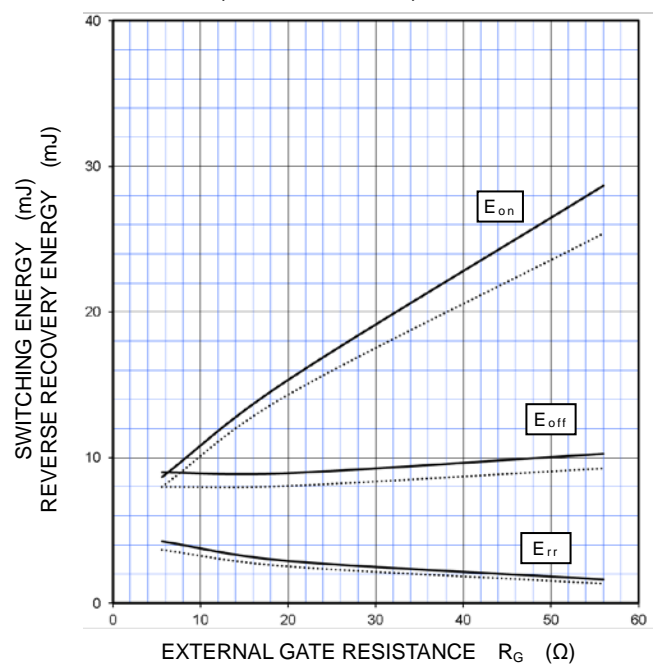
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $R_G=5.6\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_c/I_E=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



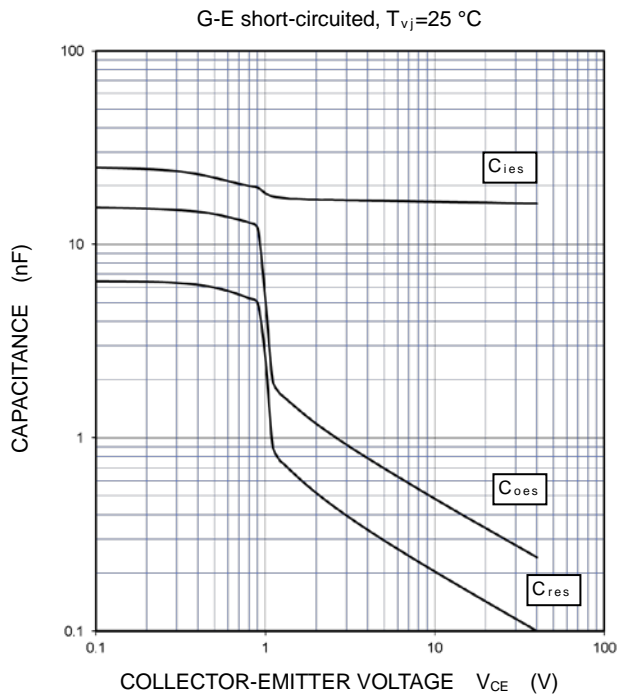
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

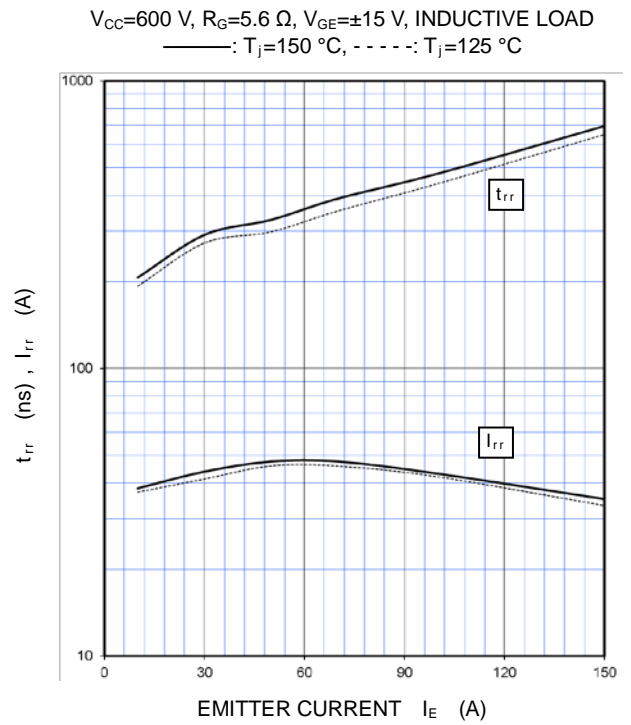
PERFORMANCE CURVES

INVERTER PART

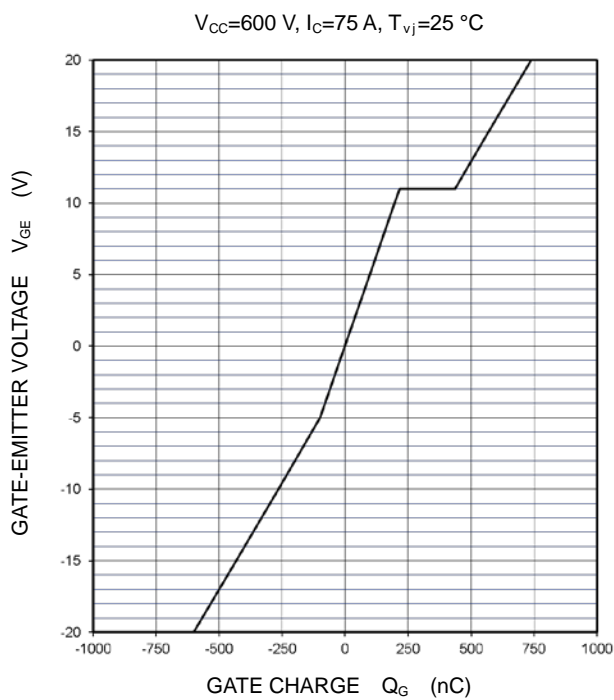
CAPACITANCE CHARACTERISTICS (TYPICAL)



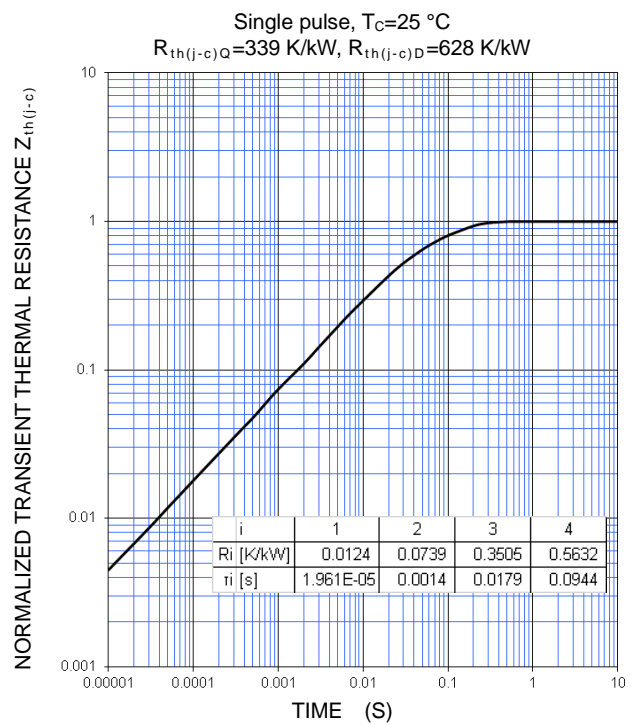
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM75MXUB-24T/CM75MXUBP-24T

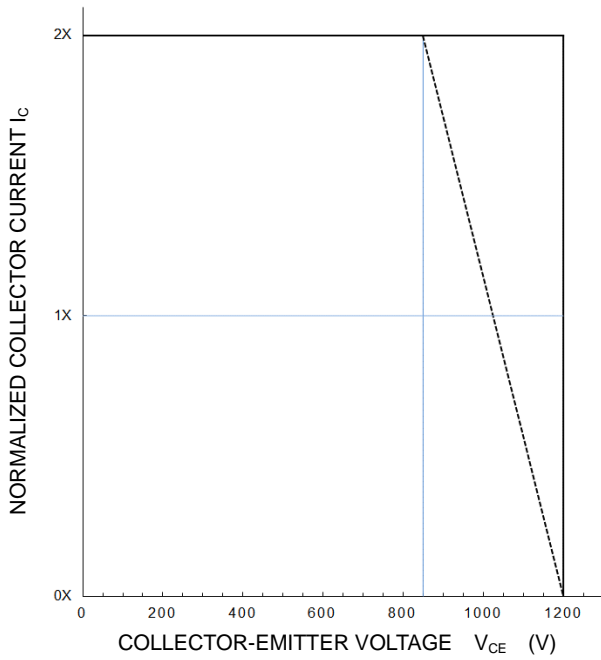
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

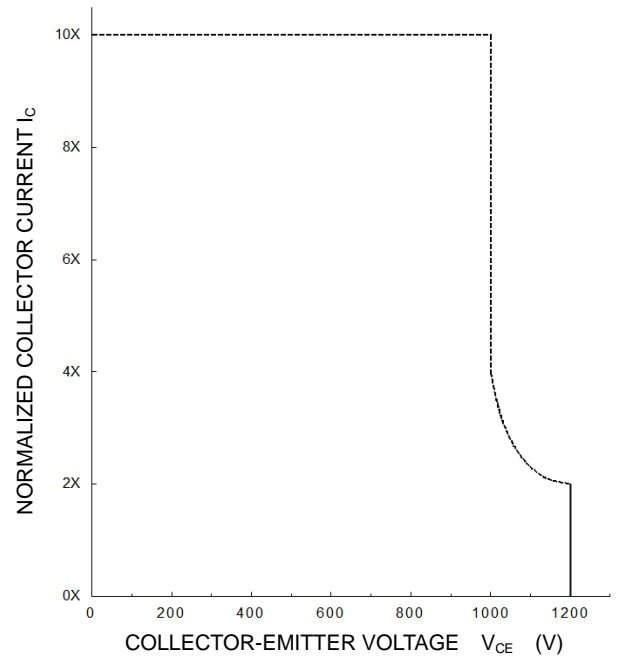
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 850 \text{ V}$, $R_G = 5.6 \sim 56 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
——: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
- - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 800 \text{ V}$, $R_G = 5.6 \sim 56 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



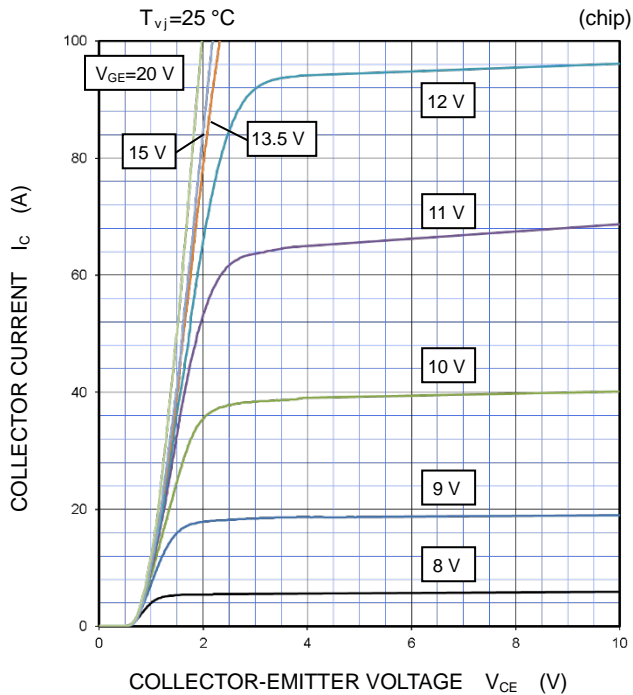
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

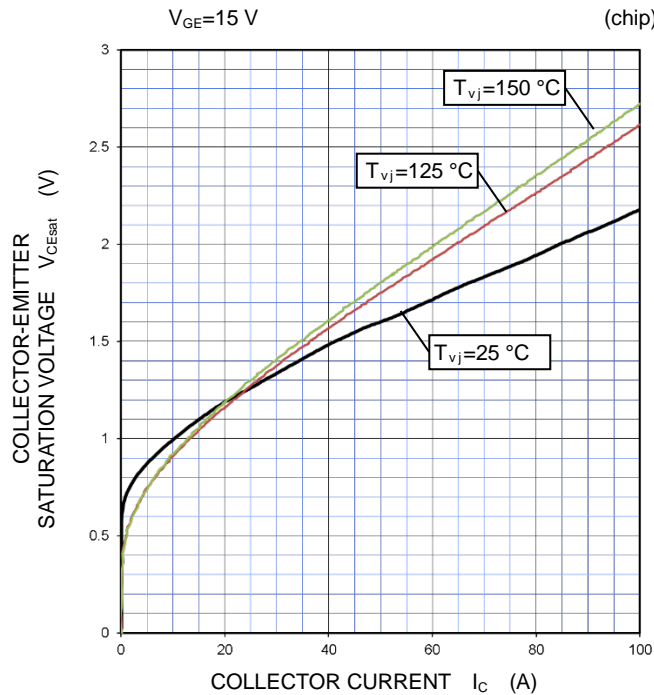
PERFORMANCE CURVES

BRAKE PART

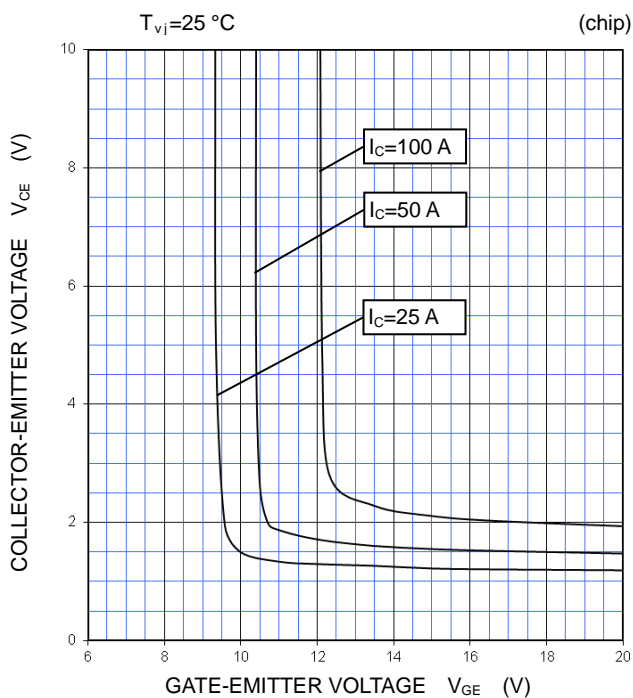
OUTPUT CHARACTERISTICS (TYPICAL)



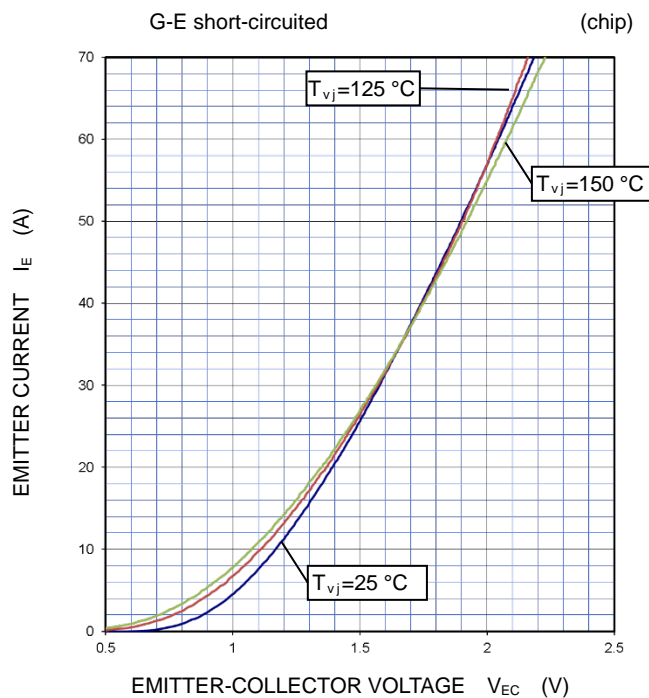
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



DIODE FORWARD CHARACTERISTICS (TYPICAL)



CM75MXUB-24T/CM75MXUBP-24T

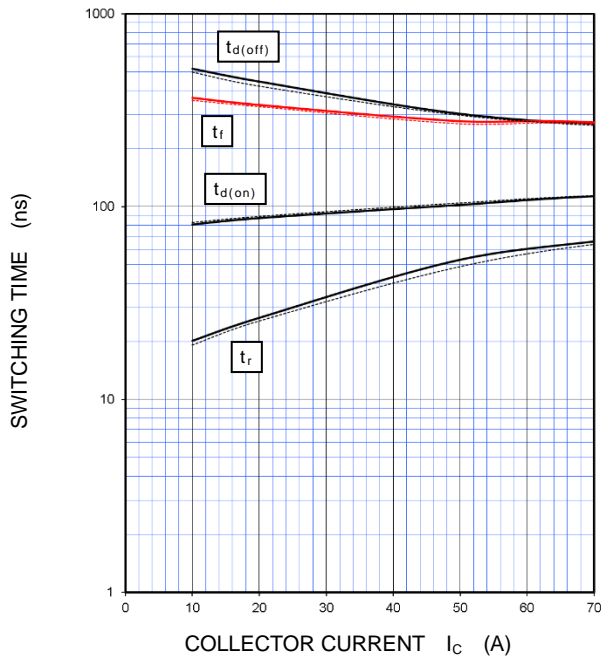
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

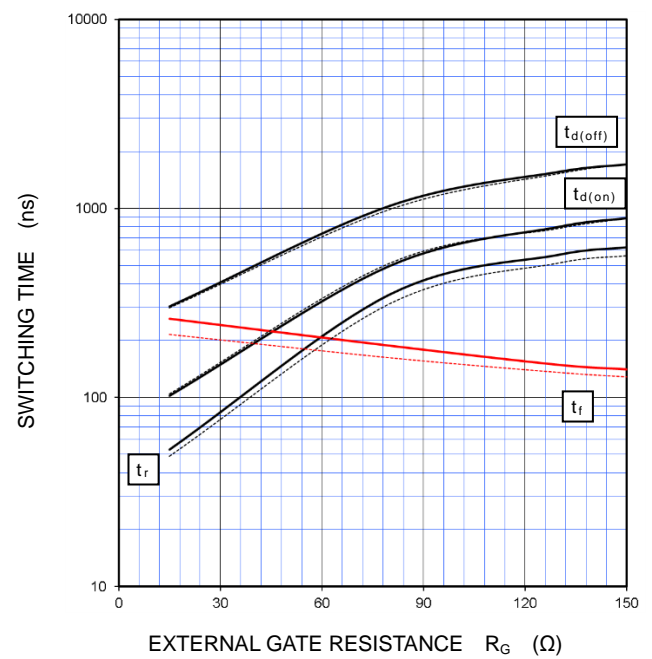
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $R_G=15\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



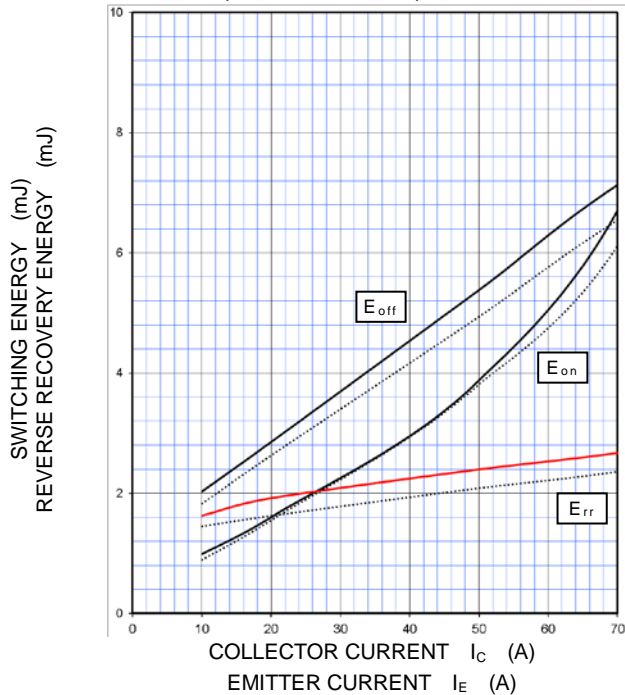
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_c=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



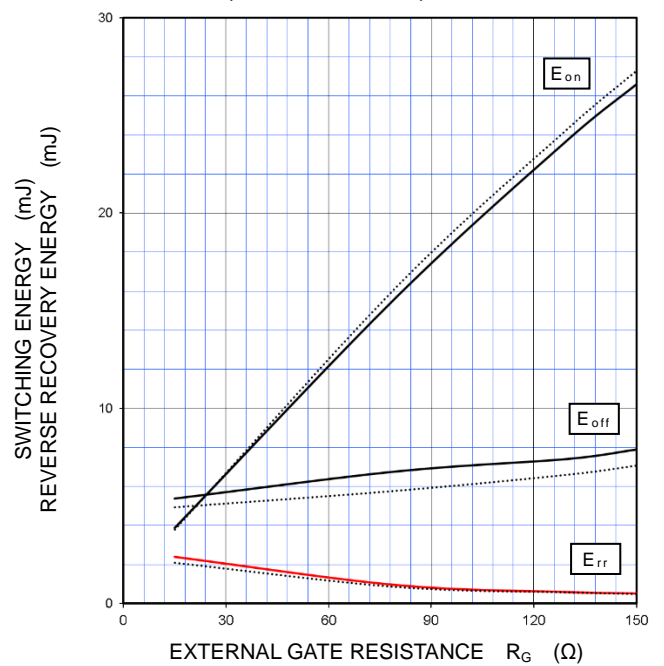
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $R_G=15\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_c/I_E=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



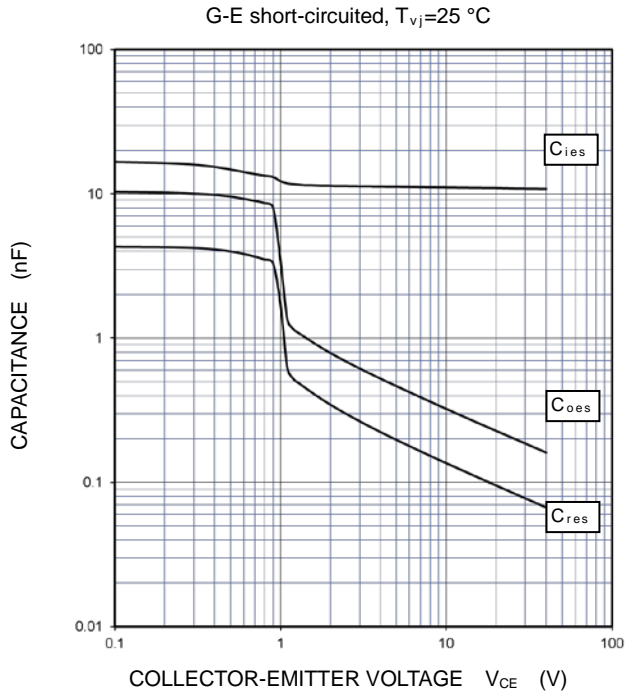
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE
INSULATED TYPE

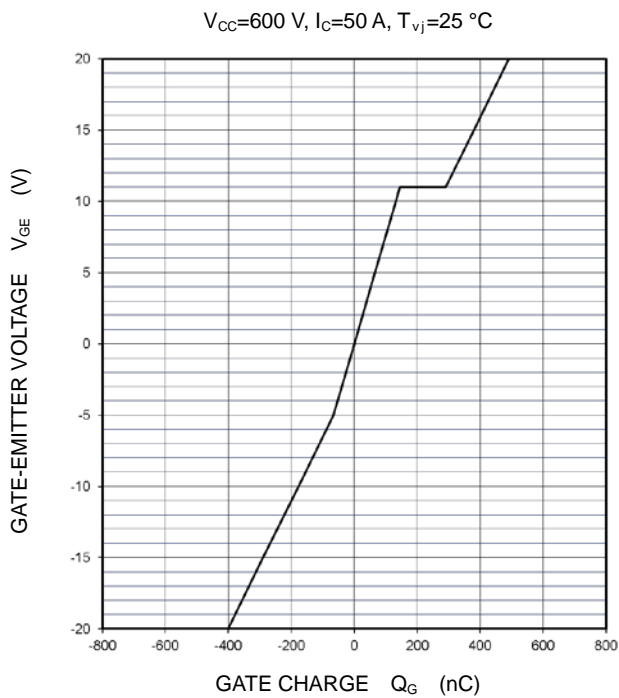
PERFORMANCE CURVES

BRAKE PART

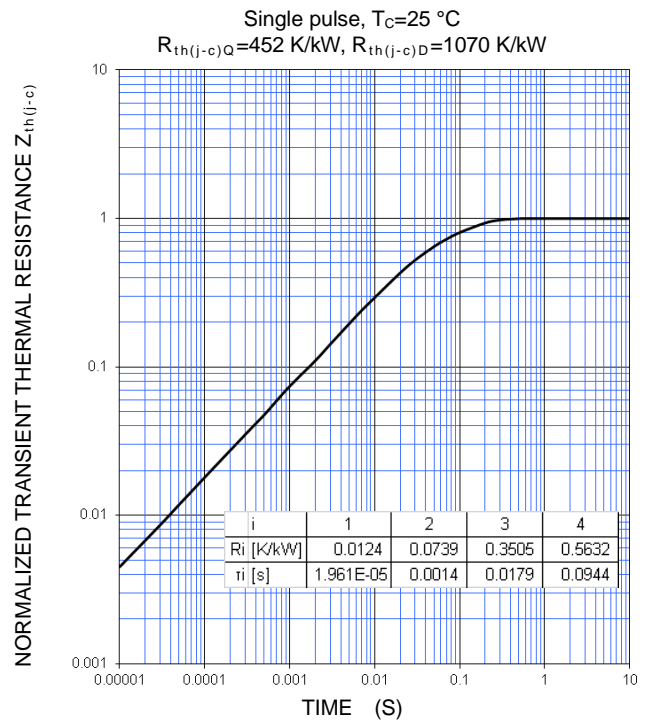
CAPACITANCE CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM75MXUB-24T/CM75MXUBP-24T

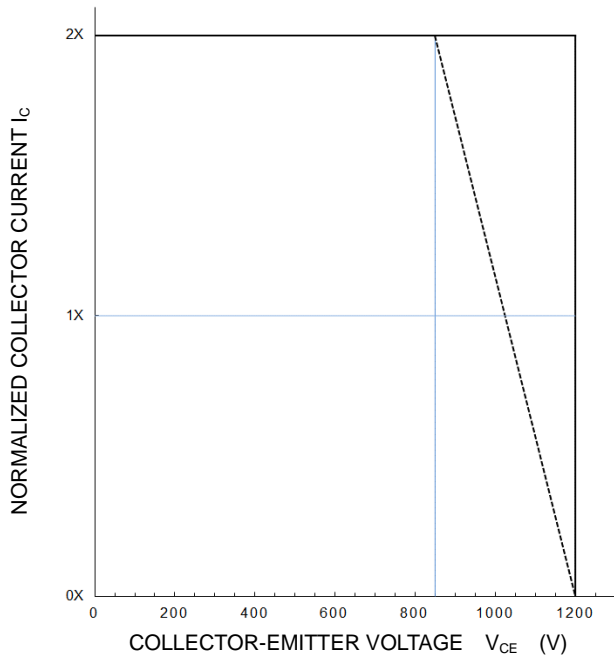
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

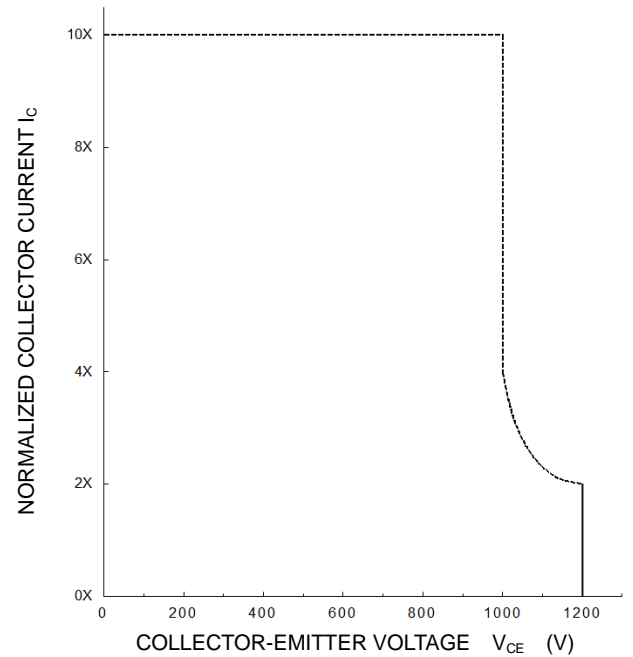
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 850 \text{ V}$, $R_G = 15 \sim 150 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 ———: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



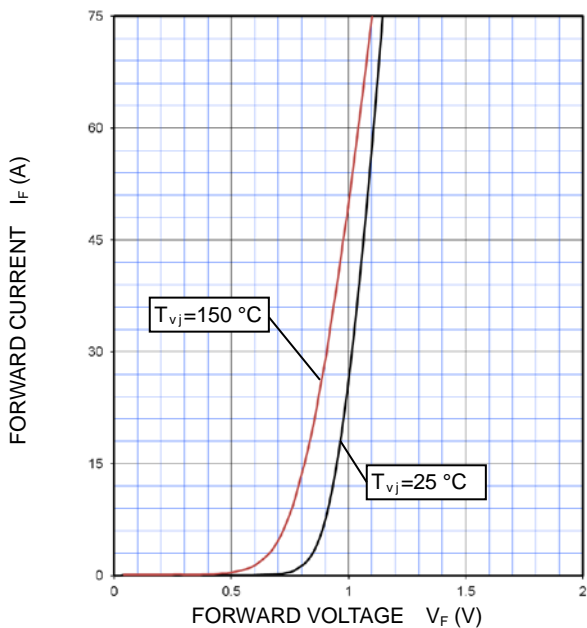
**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 800 \text{ V}$, $R_G = 15 \sim 150 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



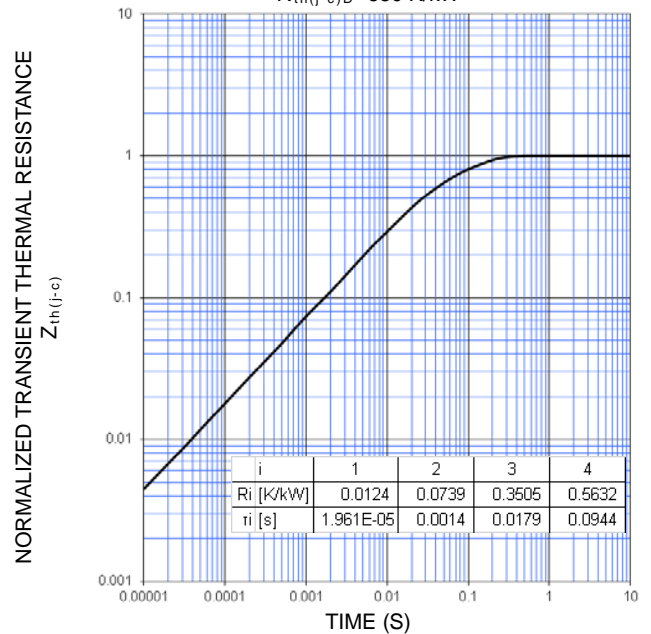
CONVERTER PART

**CONVERTER DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**

Single pulse, $T_C = 25 \text{ }^\circ\text{C}$
 $R_{th(j-c)D} = 650 \text{ K/kW}$



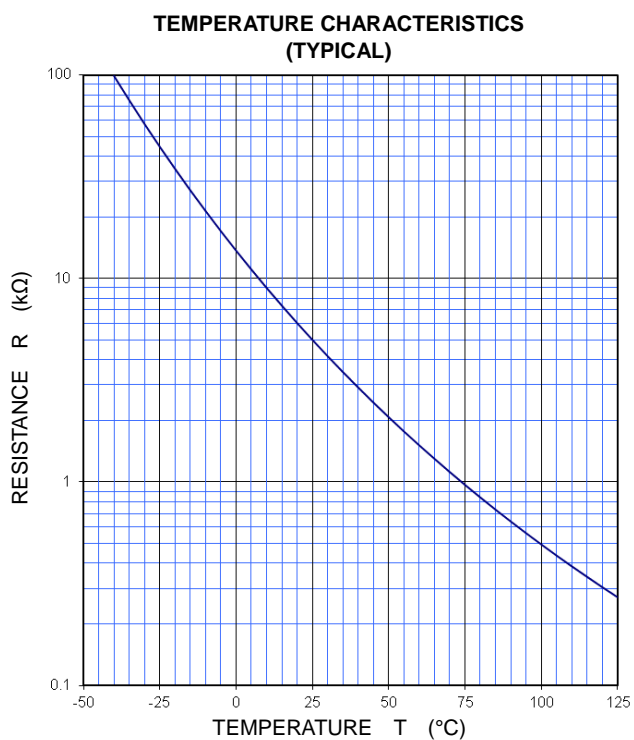
CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE

INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

CM75MXUB-24T/CM75MXUBP-24T

HIGH POWER SWITCHING USE

INSULATED TYPE

Keep safety first in your circuit designs!

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